IN THE SPECIFICATION:

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~strikethrough~~.

Please REPLACE paragraph [0012], with the following paragraph:

[0012] An ~~Axelis GSD~~Axcelis GSD™ platform implanter may be used to implant ions in the first and second wafers. The following equation may be used to estimate the rate at which neutral ions are implanted:

$I_{MEASURED} = I_{DOSE} \cdot e^{-kp}$

where $I_{MEASURED}$ is the rate at which ions are implanted, I_{DOSE} is the sum of the rate at which ions are implanted and the estimated rate at which neutral atoms are implanted, K is a pressure compensation factor and P is the pressure. A parameter P-COMP relates to the pressure compensation factor K according to the following equation:

$$K = \ln(1 + \frac{P - COMP}{100})(10000) \ .$$